Customer No.: 31561 Docket No.: 12475-US-PA Application No.: 10/710,622

## REMARKS

## Present Status of the Application

The Office Action rejected claims 1-20 and 22-31 under 35 U.S.C. 102(e) as being unpatentable by Matsumoto (US 2004/0058540) (hereinafter Matsumoto). In response thereto, Applicants respectfully traverse these rejections for at least the reasons set forth below.

The features are recited in claims 1, 10 and 22. For example, independent claim 1 recited the features.

With respect to claim 1, independent claim 1 recites the features as follows:

1. A method of correcting a lithographic process,

comprising the steps of:

performing a physical vapor deposition (PVD) process to form a thin film over a wafer, wherein an overlay mark on the wafer has a positional shift that depends on the target consumption in the PVD process and a formula relating the two can be derived;

... (Emphasis added)

Claims 22 also recite the similar features.

Matsumoto do not teach that <u>an overlay mark on the wafer has a positional shift</u>
that depends on the target consumption in the <u>PVD process</u> and a formula relating the
two can be derived." Moreover, the position information of alignment marks of each
line disclosed in Matsumoto is found by template matching method, but the present

JAN-09-2007 TUE 13:43 FAX NO. P. 05/08

Customer No.: 31561 Docket No.: 12475-US-PA Application No.: 10/710,622

invention teaches that an overlay mark on the wafer has a positional shift that depends on

the target consumption in the PVD process and a formula relating the two can be

derived. The Matsumoto fails to teach or suggest the limitation of "an overlay mark on

the wafer has a positional shift that depends on the target consumption in the PVD

process and a formula relating the two can be derived" as required by the present

invention, as set forth in claims 1 and 22. Further more, the Office Action indication

"forming a photoresist layer (item#202) over the thin film (item#203)" but in Matsumoto

reference the item #202 is exposure and the item 203 is resist treatment equipment. The

step of "forming a photoresist layer over the thin film" disclosed in claims 1 and 22 aren't

disclosed by Matsumoto.

For failing to teach each and every limitation of claim 1 and 22, Matsumoto does

not prima facie anticipate the claimed invention, as set forth in claims 1, 22 and its

dependent claims 2-9, and 23-31. Claims 2-9, and 23-31 are therefore submitted to be

novel and unobvious over Matsumoto, or any of the other cited references, taken alone or

in combination, and thus should be allowed.

With respect to claim 10, independent claim 10 recites the features as follows:

10. A method of forming an overlay mark on a wafer

having a material layer thereon, comprising the steps of:

performing a physical vapor deposition (PVD) process to form a second

film layer over the first film layer, wherein the deposited second film

layer causes a shift in an overlay mark such that the degree of shifting

3

PAGE 5/8 \* RCVD AT 1/9/2007 12:41:22 AM [Eastern Standard Time] \* SVR:USPTO-EFXRF-6/39 \* DNIS:2738300 \* CSID: \* DURATION (mm-ss):01-50

JAN-09-2007 TUE 13:43 FAX NO. P. 06/08

Customer No.: 31561 Docket No.: 12475-US-PA

Application No.: 10/710.622

is related to the target consumption in the PVD process and a formula

relating the two can be derived;

... (Emphasis added)

Matsumoto do not teach that the deposited second film laver causes a shift in an

overlay mark such that the degree of shifting is related to the target consumption in the

PVD process and a formula relating the two can be derived." Moreover, the position

information of alignment marks of each line disclosed in Matsumoto is found by template

matching method, but the present invention teaches that the deposited second film layer

causes a shift in an overlay mark such that the degree of shifting is related to the target

consumption in the PVD process and a formula relating the two can be derived. The

Matsumoto fails to teach or suggest the limitation of "the deposited second film laver

causes a shift in an overlay mark such that the degree of shifting is related to the target

consumption in the PVD process and a formula relating the two can be derived" as

required by the present invention, as set forth in claim 10.

For failing to teach each and every limitation of claim 10, Matsumoto does not

prima facie anticipate the claimed invention, as set forth in claims 10 and its dependent

claims 11-21. Claims 11-21 are therefore submitted to be novel and unobvious over

Matsumoto, or any of the other cited references, taken alone or in combination, and thus

should be allowed.

For at least the foregoing reasons, Applicants respectfully submit that independent

4

Customer No.: 31561 Docket No.: 12475-US-PA Application No.: 10/710,622

claims 1, 10 and 22 patently define over the prior art reference, and should be allowed. For at least the same reasons, dependent claims 2-9, 11-21 and 23-31 patently define over the prior art as a matter of law.

Customer No.: 31561 Docket No.: 12475-US-PA Application No.: 10/710,622

## CONCLUSION

In view of the foregoing, it is believed that all pending claims are in proper condition for allowance. If the Examiner believes that a conference would be of value in expediting the prosecution of this application, he is cordially invited to telephone the undersigned counsel to arrange for such a conference.

Date:

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Respectfully submitted,

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